Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} \leq 127 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	10	Α
Static characte	eristics						
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.3	2	V
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	12	18	ns





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	$rac{1}{2}$	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC10-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC10-600P	BYC10-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	$\bar{\delta}$ = 0.5; T _{mb} ≤ 127 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 127 °C; square-wave pulse	-	20	А

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Symbol	Parameter	Conditions	Min	Max	Unit
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>	-	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>	-	165	Α
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C

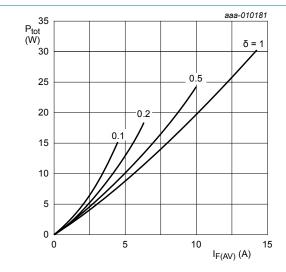


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$
 $V_{\rm O} = 1.572\,{\rm V};\,{\rm R_S} = 0.040\,\Omega$

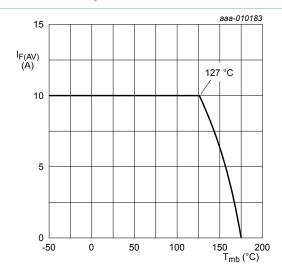


Fig. 3. Forward current as a function of mounting base temperature; maximum values

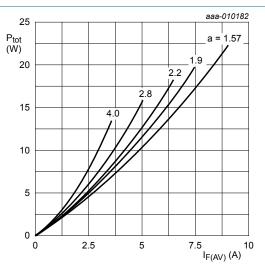


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

 $V_{\odot} = 1.572 \text{ V}; R_{S} = 0.040 \Omega$

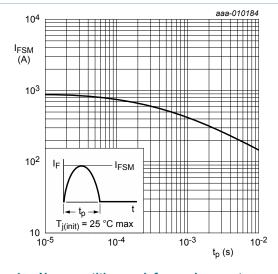


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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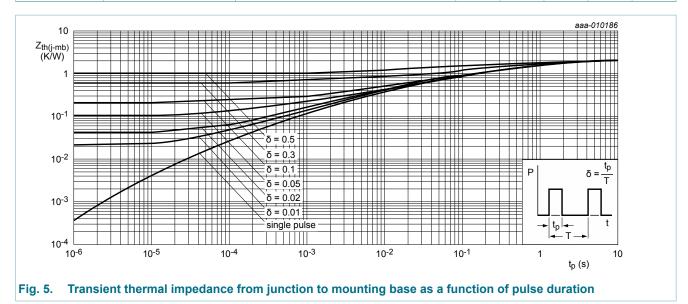
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V_{F}	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.3	2	V
I _R reverse curi	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	0.8	mA
Dynamic cl	haracteristics					
Q _r recovered charg	recovered charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	26	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 \text{ °C}; Fig. 7$	-	83	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	12	18	ns
		$I_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 500 \text{ A/}$ $\mu \text{s; } T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	19	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 \text{ °C}; Fig. 7$	-	26	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	34	-	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 \text{ °C}; Fig. 7$	-	2	-	А
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	4.8	-	A

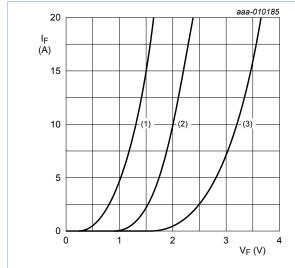


Fig. 6. Forward current as a function of forward voltage

(1) T_j = 150 °C; typical values; (2) T_j = 150 °C; maximum values; (3) T_j = 25 °C; maximum values; V_O = 1.572 V; R_S = 0.040 Ω

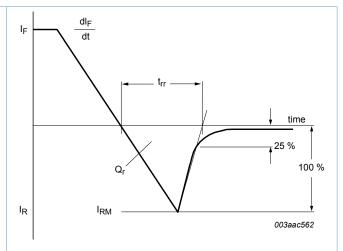
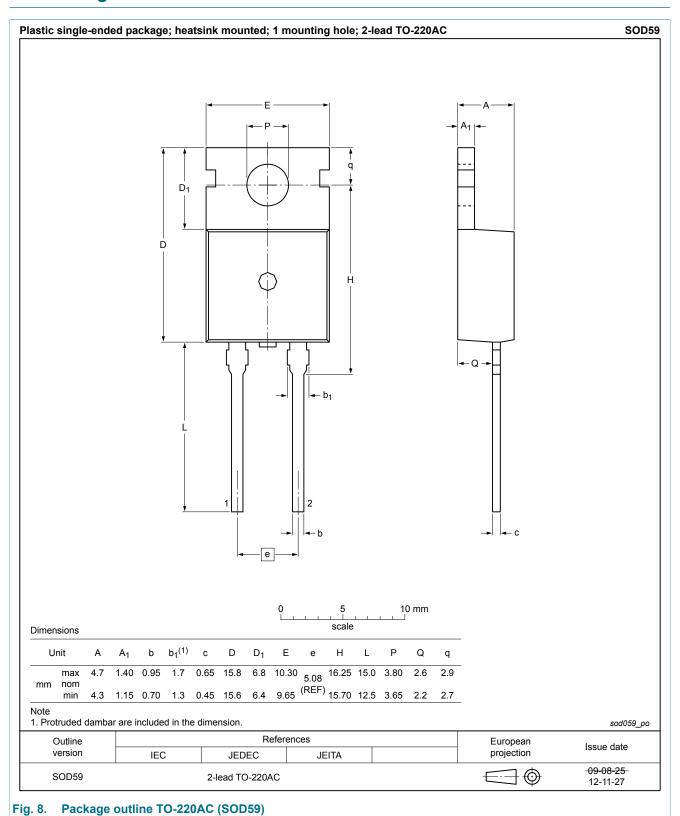


Fig. 7. Reverse recovery definitions; ramp recovery

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11. Package outline



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12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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